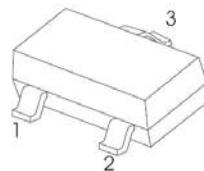


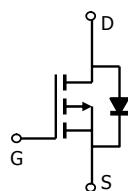
■ Features

- $V_{DS}$  (V) = -30V
- $I_D$  = -2.6 A ( $V_{GS}$  = -10V)
- $R_{DS(ON)} < 130\text{m}\Omega$  ( $V_{GS}$  = -10V)
- $R_{DS(ON)} < 200\text{m}\Omega$  ( $V_{GS}$  = -4.5V)
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

**SOT - 23**



1. GATE
2. SOURCE
3. DRAIN



■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D$	-2.6	A
$T_a = 70^\circ\text{C}$		-2.2	
Pulsed Drain Current	$I_{DM}$	-20	
Power Dissipation	$P_D$	1.4	W
$T_a = 70^\circ\text{C}$		1	
Thermal Resistance. Junction-to-Ambient	$R_{thJA}$	125	$^\circ\text{C}/\text{W}$
Thermal Resistance. Junction-to-Case	$R_{thJC}$	80	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D=250 \mu\text{A}, V_{GS}=0\text{V}$	-30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-24\text{V}, V_{GS}=0\text{V}$			-1	$\mu\text{A}$
		$V_{DS}=-24\text{V}, V_{GS}=0\text{V}, TJ=55^\circ\text{C}$			-5	
Gate-Body leakage current	$I_{GSS}$	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(\text{th})}$	$V_{DS}=V_{GS}, I_D=-250 \mu\text{A}$	-1	-1.9	-3	V
Static Drain-Source On-Resistance	$r_{DS(\text{ON})}$	$V_{GS}=-10\text{V}, I_D=-2.6\text{A}$		97	130	$\text{m}\Omega$
		$V_{GS}=-10\text{V}, I_D=-2.6\text{A}, TJ=125^\circ\text{C}$		135	150	
		$V_{GS}=-4.5\text{V}, I_D=-2\text{A}$		166	200	
On state drain current	$I_{D(\text{ON})}$	$V_{GS}=-4.5\text{V}, V_{DS}=-5\text{V}$	-5			A
Forward Transconductance	$g_{fs}$	$V_{DS}=-5\text{V}, I_D=-5\text{A}$	3	3.8		S
Input Capacitance	$C_{iss}$	$V_{GS}=0\text{V}, V_{DS}=-15\text{V}, f=1\text{MHz}$		302	370	pF
Output Capacitance	$C_{oss}$			50.3		pF
Reverse Transfer Capacitance	$C_{rss}$			37.8		pF
Gate resistance	$R_g$	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$		12	18	$\Omega$
Total Gate Charge (10V)	$Q_g$	$V_{GS}=-4.5\text{V}, V_{DS}=-15\text{V}, I_D=-2.6\text{A}$		6.8	9	nC
Total Gate Charge (4.5V)				2.4		nC
Gate Source Charge	$Q_{gs}$			1.6		nC
Gate Drain Charge	$Q_{gd}$			0.95		nC
Turn-On DelayTime	$t_{D(\text{on})}$			7.5		ns
Turn-On Rise Time	$t_r$	$V_{GS}=-10\text{V}, V_{DS}=-15\text{V}, R_L=5.8\Omega, R_{GEN}=3\Omega$		3.2		ns
Turn-Off DelayTime	$t_{D(\text{off})}$			17		ns
Turn-Off Fall Time	$t_f$			6.8		ns
Body Diode Reverse Recovery Time	$t_{rr}$			16.8	22	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F=-2.6\text{A}, dI/dt=100\text{A}/\mu\text{s}$		10		nC
Maximum Body-Diode Continuous Current	$I_s$				-2	A
Diode Forward Voltage	$V_{SD}$	$I_s=-1\text{A}, V_{GS}=0\text{V}$		-0.82	-1	V

\* Repetitive rating, pulse width limited by junction temperature.

■ Typical Characteristics

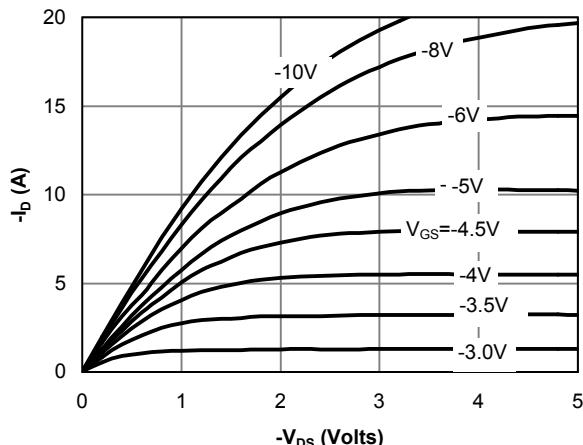


Fig 1: On-Region Characteristics

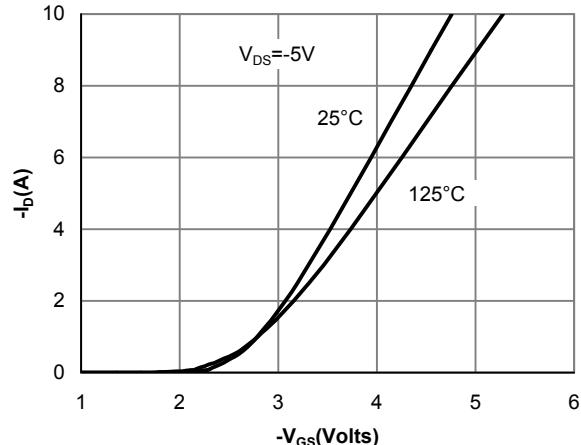


Figure 2: Transfer Characteristics

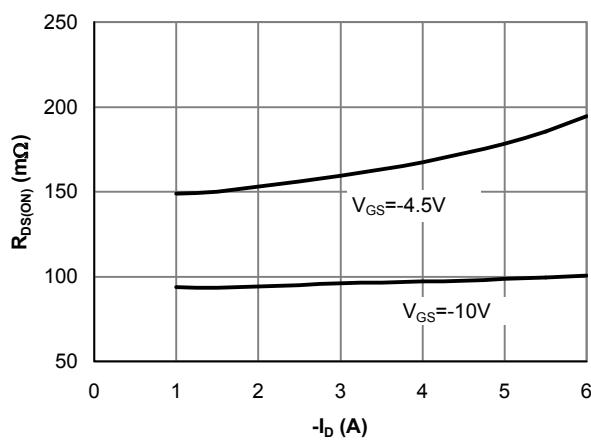


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

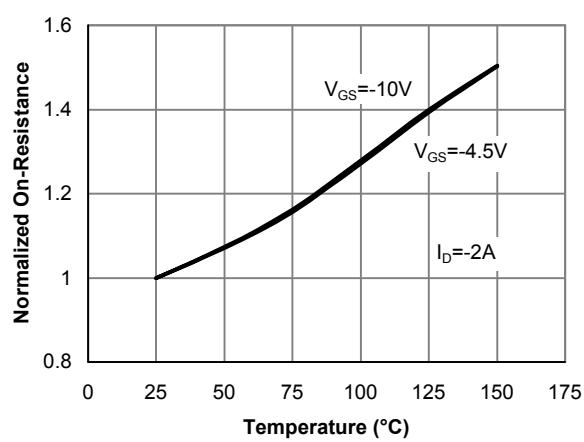


Figure 4: On-Resistance vs. Junction Temperature

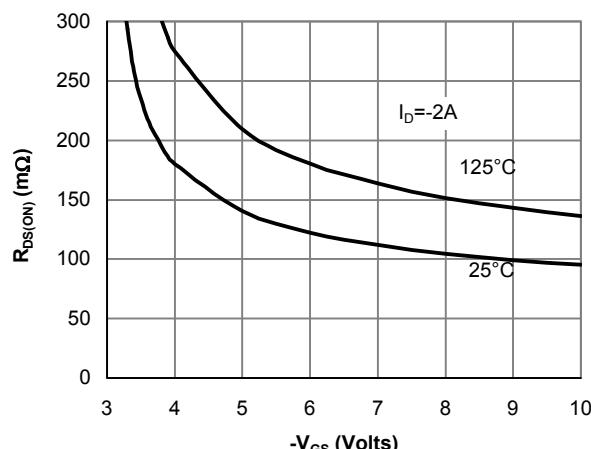


Figure 5: On-Resistance vs. Gate-Source Voltage

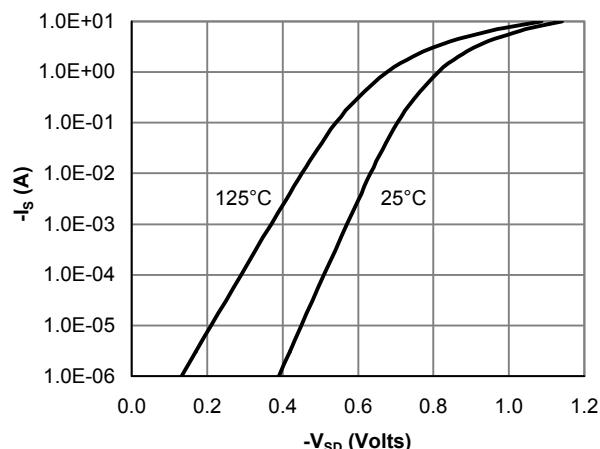
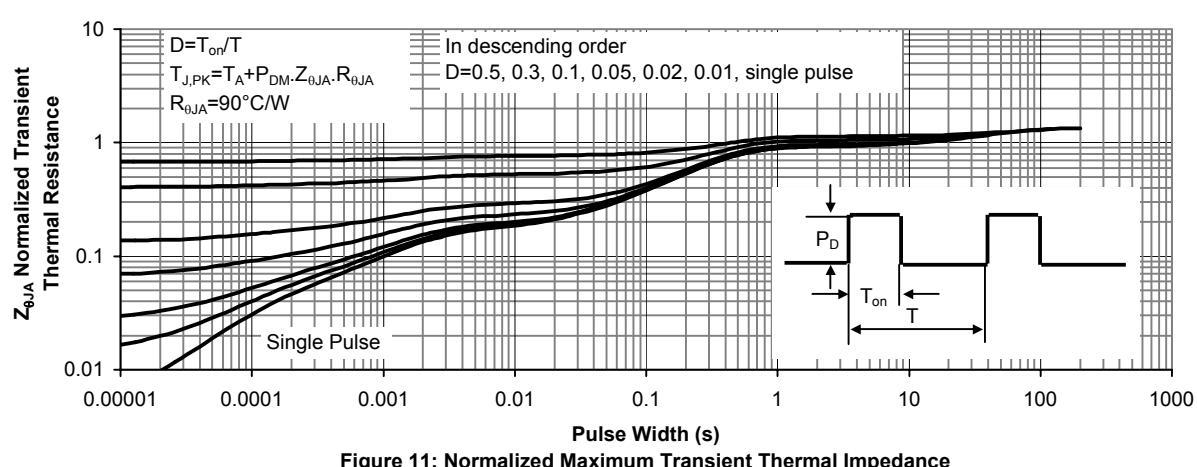
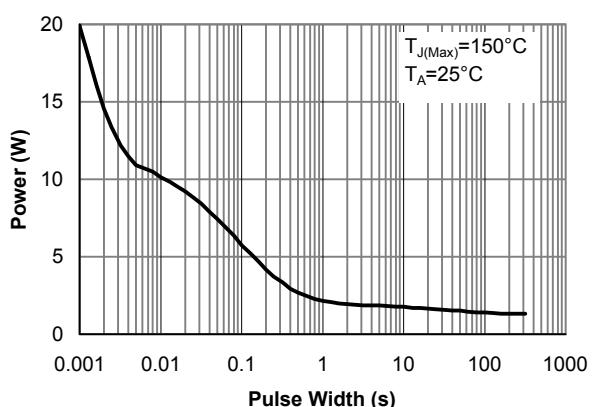
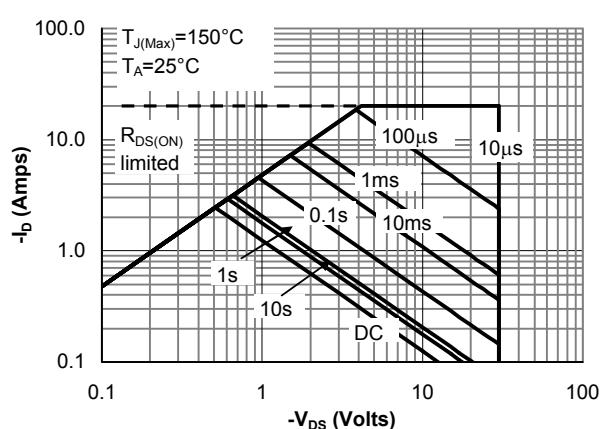
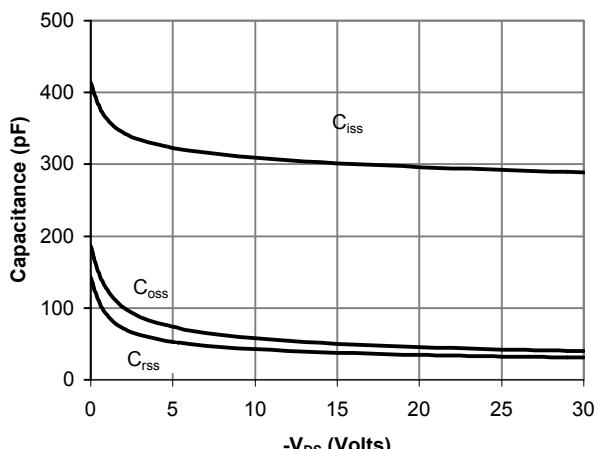
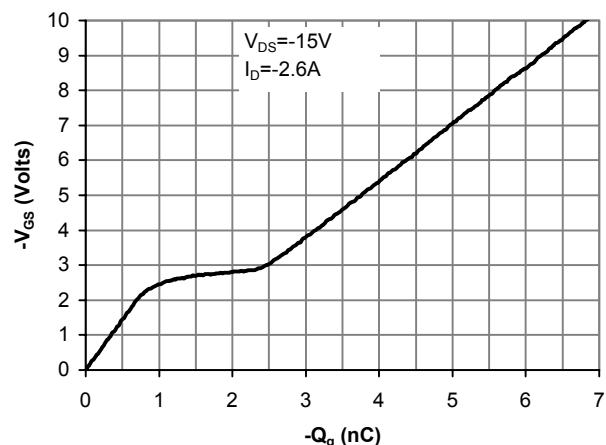
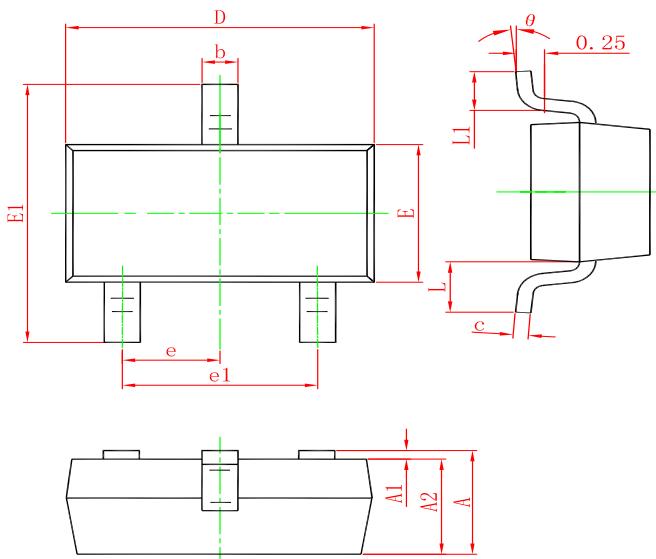


Figure 6: Body-Diode Characteristics

■ Typical Characteristics



## SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

## Marking



## Ordering information

Order code	Package	Baseqty	Deliverymode
UMW AO3409A	SOT-23	3000	Tape and reel